





600V HALF BRIDGE GATE DRIVER IN SO-8

Description

The DGD2184M is a high-voltage and high-speed gate driver capable of driving N-Channel MOSFETs and IGBTs in a half bridge configuration. High-voltage processing techniques enable the DGD2184M's high-side to switch to 600V in a bootstrap operation.

The DGD2184M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) for easy interfacing with controlling devices. The driver outputs feature high-pulse current buffers designed for minimum driver cross conduction. The DGD2184M has a fixed internal deadtime of 395ns (typ).

The DGD2184M is offered in the SO-8 (Type TH) package, and the operating temperature extends from -40°C to +125°C.

Applications

- DC-DC converters
- DC-AC inverters
- AC-DC power supplies
- Motor controls
- Class D power amplifiers

Typical Configuration

Features

- Floating High-Side Driver in Bootstrap Operation to 600V
- Drives Two N-Channel MOSFETs or IGBTs in Half Bridge Configuration
- 1.9A Source / 2.3A Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 395ns to Protect MOSFETs
- Wide Low-Side Gate Driver and Logic Supply: 10V to 20V
- Logic Input (IN and SD*) 3.3V Capability
- Schmitt Triggered Logic Inputs with Internal Pull Down
- Undervoltage Lockout for High- and Low-Side Drivers
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SO-8 (Type TH)
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.075 grams (Approximate)



Top View

Ordering Information (Note 4)

Orderable Part Number	Packago	Marking	Reel Size (inch)	Tape Width (mm)	(mm) Packing	
Orderable Part Number	Fackage	Package Marking Reel Size (inch) Tape Width (mm	rape widin (min)	Qty.	Carrier	
DGD2184MS8-13	SO-8 (Type TH)	DGD2184M	13	12	2,500	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

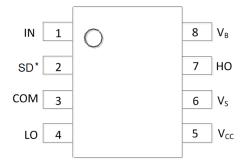
Marking Information



)¦¦ = Manufacturer's Marking DGD2184M = Product Type Marking Code YY = Year (ex: 23 = 2023) WW = Week (01 to 53)



Pin Diagrams

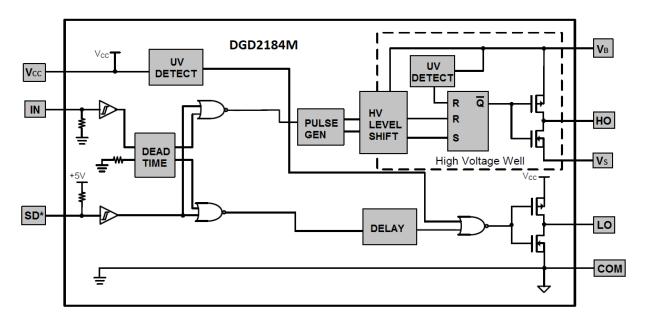


Top View SO-8

Pin Descriptions

Pin Number	Pin Name	Function
1	IN	Logic Input for High-Side and Low-Side Gate Driver Outputs (HO and LO), in Phase with HO
2	SD*	Logic Input for Shutdown, Enabled Low
3	COM	Low-Side and Logic Return
4	LO	Low-Side Gate Drive Output
5	Vcc	Low-Side and Logic Fixed Supply
6	Vs	High-Side Floating Supply Return
7	НО	High-Side Gate Drive Output
8	V _B	High-Side Floating Supply

Functional Block Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V _B	-0.3 to +624	V
High-Side Floating Supply Offset Voltage	Vs	$V_B - 24 \text{ to } V_B + 0.3$	V
High-Side Floating Output Voltage	V _{HO}	$V_S - 0.3$ to $V_B + 0.3$	V
Offset Supply Voltage Transient	dV _S / dt	50	V/ns
Low-Side Fixed Supply Voltage	V _{CC}	-0.3 to +24	V
Low-Side Output Voltage	V _{LO}	-0.3 to V _{CC} + 0.3	V
Logic Input Voltage (IN and SD*)	V _{IN}	-0.3 to V _{CC} + 0.3	V

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	0.625	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	200	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	T _L	+300	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V_{B}	V _S + 10	V _S + 20	٧
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	600	V
High-Side Floating Output Voltage	V_{HO}	Vs	V_{B}	V
Low-Side Fixed Supply Voltage	V _{CC}	10	20	V
Low-Side Output Voltage	V_{LO}	0	Vcc	V
Logic Input Voltage (IN and SD*)	V_{IN}	0	V _{CC}	V
Ambient Temperature	T _A	-40	+125	°C

Note: 6. Logic operation for V_S of -5V to +600V.



$\textbf{DC Electrical Characteristics} \ (V_{BIAS} \ (V_{CC}, \ V_{BS}) = 15 V, \ @T_A = +25 ^{\circ}C, \ unless \ otherwise \ specified.) \ (Note \ 7)$

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage	V_{IH}	2.5	_	_	V	$V_{CC} = 10V \text{ to } 20V$
Logic "0" Input Voltage	V_{IL}	_	_	0.8	V	$V_{CC} = 10V \text{ to } 20V$
SD* Input Positive Going Threshold	V_{SDTH+}	2.5	_	_	V	$V_{CC} = 10V \text{ to } 20V$
SD* Input Negative Going Threshold	V _{SDTH} -	_	_	0.8	V	$V_{CC} = 10V \text{ to } 20V$
High Level Output Voltage, V _{BIAS} – V _O	V _{OH}	_	_	1.2	V	$I_O = 0mA$
Low Level Output Voltage, Vo	V_{OL}	_	_	0.1	V	$I_O = 20mA$
Offset Supply Leakage Current	I _{LK}	_	_	50	μΑ	$V_B = V_S = 600V$
Quiescent V _{BS} Supply Current	I _{BSQ}	20	60	150	μΑ	$V_{IN} = 0V \text{ or } 5V$
Quiescent V _{CC} Supply Current	Iccq	0.4	1.0	1.8	mA	$V_{IN} = 0V \text{ or } 5V$
Logic "1" Input Bias Current	I _{IN+}	_	25	60	μΑ	$IN = 5V, SD^* = 0V$
Logic "0" Input Bias Current	I _{IN-}	_	_	1.0	μΑ	$IN = 0V, SD^* = 5V$
V _{BS} Supply Under-Voltage Positive Going Threshold	V _{BSUV+}	8.0	8.9	9.8	V	_
V _{BS} Supply Under-Voltage Negative Going Threshold	V_{BSUV}	7.4	8.2	9.0	V	
V _{CC} Supply Under-Voltage Positive Going Threshold	V _{CCUV+}	8.0	8.9	9.8	V	_
V _{CC} Supply Under-Voltage Negative Going Threshold	V _{CCUV} -	7.4	8.2	9.0	V	_
Output High Short Circuit Pulsed Current	I _{O+}	1.4	1.9	_	Α	V _O = 0V, PW ≤ 10μs
Output Low Short Circuit Pulsed Current	l ₀₋	1.7	2.3	_	Α	V _O = 15V, PW ≤ 10μs

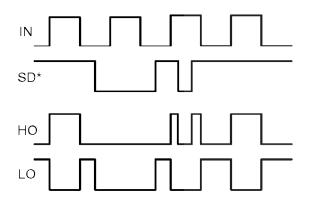
Note: 7. The V_{IN} and I_{IN} parameters are applicable to the two logic input pins: IN and SD*. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

$\textbf{AC Electrical Characteristics} \ (V_{BIAS} \ (V_{CC}, \ V_{BS}) = 15 \text{V}, \ C_L = 1000 \text{pF}, \ @T_A = +25 ^{\circ}\text{C}, \ unless otherwise specified.})$

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-On Propagation Delay	ton	_	585	900	ns	$V_S = 0V$
Turn-Off Propagation Delay	t _{off}	_	170	400	ns	V _S = 0V or 600V
Shut-Down Propagation Delay	t _{SD}	_	180	270	ns	_
Delay Matching, HO & LO Turn-On	t _{DMON}	_	_	90	ns	_
Delay Matching, HO & LO Turn-Off	t _{DMOFF}	_	_	40	ns	$I_O = 0A$
Turn-On Rise Time	t _r	_	40	60	ns	$V_S = 0V$
Turn-Off Fall Time	t _f	_	20	35	ns	$V_S = 0V$
Deadtime: t _{DT LO-HO &} t _{DT HO-LO}	t _{DT}	345	395	445	ns	_



Timing Waveforms



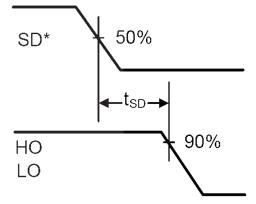
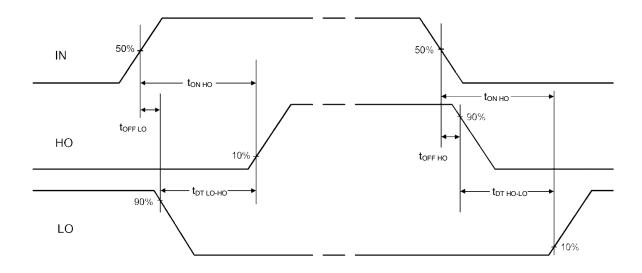


Figure 1. Input / Output Timing Diagram

Figure 2. Shutdown Waveform Definitions



Deadtime t_{DT LO-HO} = t_{ON HO} - t_{OFF LO}
t_{DT HO-LO} = t_{ON LO} - t_{OFF HO}
Deadtime matching
t_{MDT} = t_{DT LO-HO} - t_{DT HO-LO}

Delay matching t_{DM OFF} = t_{OFF} LO - t_{OFFT} HO

Figure 3. Switching Time Waveform Definitions



Typical Performance Characteristics (@T_A = +25°C, V_{CC} = 15V, unless otherwise specified.)

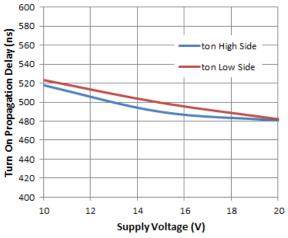


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

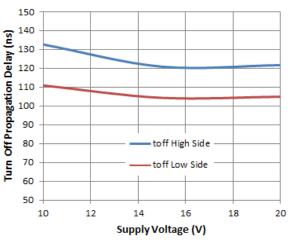


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

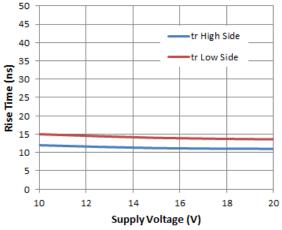


Figure 8. Rise Time vs. Supply Voltage

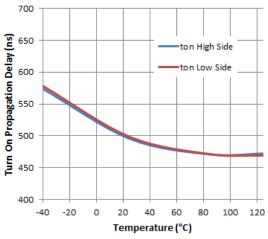


Figure 5. Turn-on Propagation Delay vs. Temperature

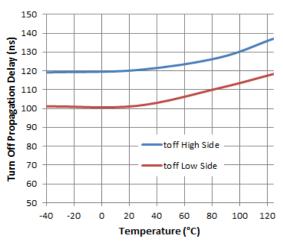


Figure 7. Turn-off Propagation Delay vs. Temperature

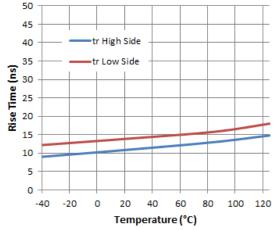


Figure 9. Rise Time vs. Temperature



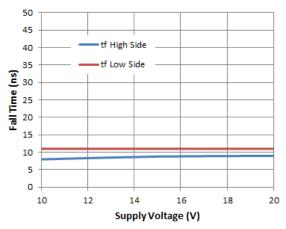


Figure 10. Fall Time vs. Supply Voltage

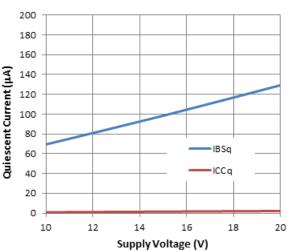


Figure 12. Quiescent Current vs. Supply Voltage

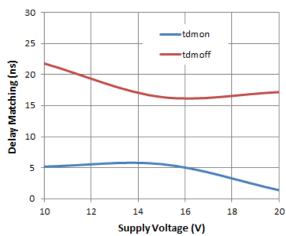


Figure 14. Delay Matching vs. Supply Voltage

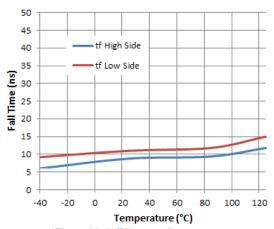


Figure 11. Fall Time vs. Temperature

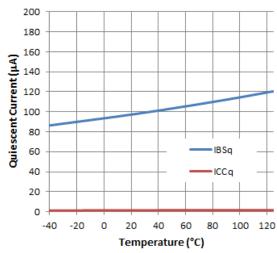


Figure 13. Quiescent Current vs. Temperature

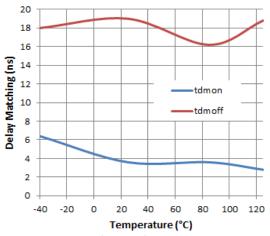


Figure 15. Delay Matching vs. Temperature



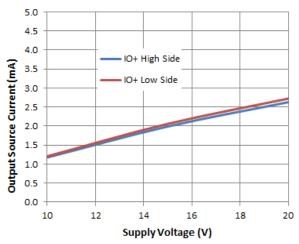


Figure 16. Output Source Current vs. Supply Voltage

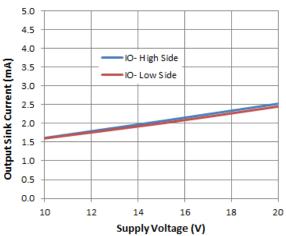


Figure 18. Output Sink Current vs. Supply Voltage

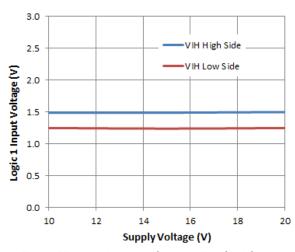


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

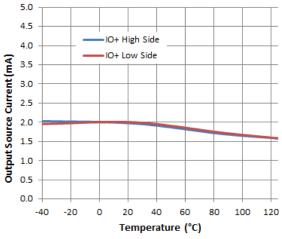


Figure 17. Output Source Current vs. Temperature

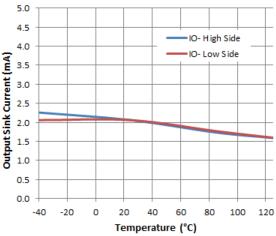


Figure 19. Output Sink Current vs. Temperature

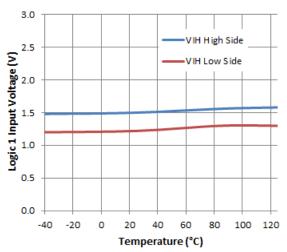


Figure 21. Logic 1 Input Voltage vs. Temperature



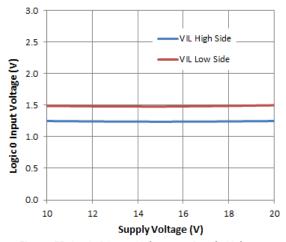


Figure 22. Logic O Input Voltage vs. Supply Voltage

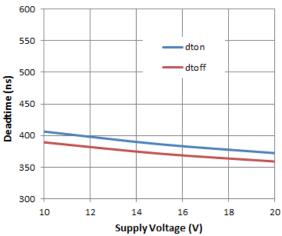


Figure 24. Deadtime vs. Supply Voltage

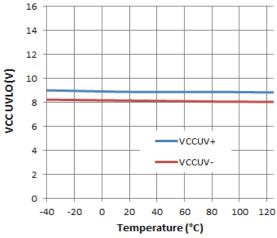


Figure 26. VCC UVLO vs. Temperature

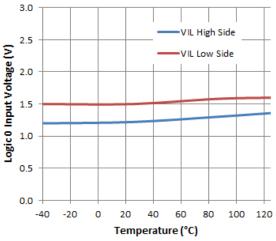


Figure 23. Logic 0 Input Voltage vs. Temperature

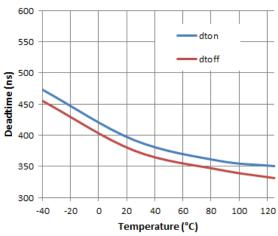


Figure 25. Deadtime vs. Temperature

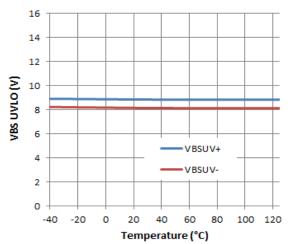


Figure 27. VBS UVLO vs. Temperature



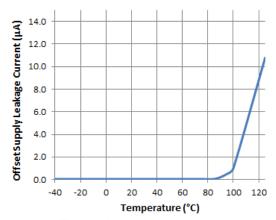


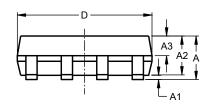
Figure 28. Offset Supply Leakage Current vs. Temperature



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)





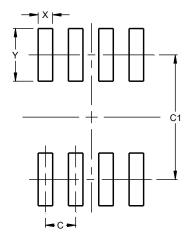
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	SO-8 (Type TH)					
Dim	Min	Max	Тур			
Α		1.75				
A1	0.10	0.225				
A2	1.30	1.50	1.40			
A3	0.60	0.70	0.65			
b	0.39	0.47				
C	0.20	0.24				
D	4.80	5.00	4.90			
Е	5.80	6.20	6.00			
E1	3.80	4.00	3.90			
е	1	.27BSC	;			
h	0.25	0.50				
L	0.50 0.80					
L1	1.05REF					
а	0°	8°				
All [Dimensi	ons in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8 (Type TH)



Dimensions	Value (in mm)
С	1.27
C1	5.20
Х	0.60
V	2 20



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